

Supporting Information

Resistive switching behavior in α - In_2Se_3 nanoflakes modulated by ferroelectric polarization and interface defects

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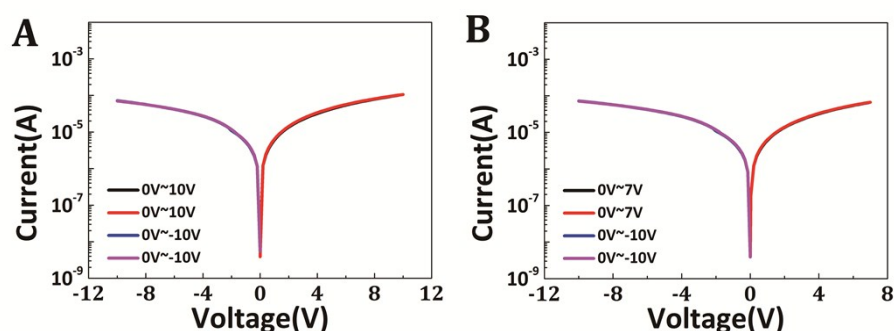


Figure R1. Current of Pt/ α - In_2Se_3 /Pt device at various applied voltage in dark.

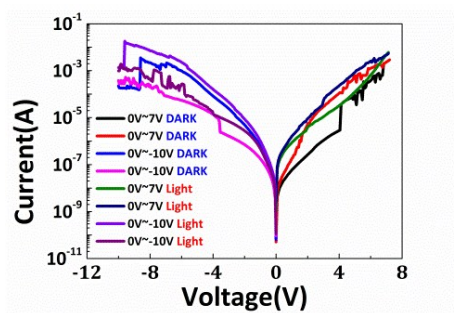


Figure R3. I-V curves under dark and light illumination.

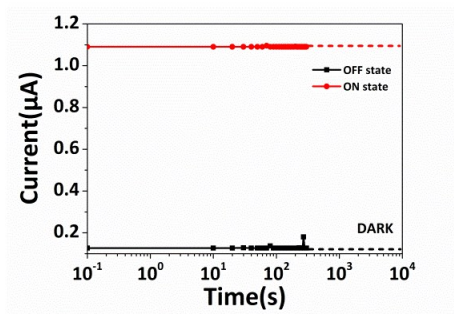


Figure R2. Current of Pt/ α - In_2Se_3 /Pt device as a function of time in dark.